








	<h2 style="color: red;">FQB5N30TM</h2>
 <p>Image may be representation. See specs for product details.</p>	<b>Hersteller-Teilenummer:</b> <a href="#">FQB5N30TM</a>
	<b>Hersteller / Marke:</b> <a href="#">Fairchild/ON Semiconductor</a>
	<b>Teil der Beschreibung:</b> MOSFET N-CH 300V 5.4A D2PAK
	<b>Datenblätter:</b>  <a href="#">FQB5N30TM.pdf</a>
	<b>RoHs Status:</b> Bleifrei / RoHS-konform
	<b>Lagerzustand:</b> New original, 1450 pcs Stock Available.
	<b>Liefern von:</b> Hong Kong
<b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS	

### Spezifikationen

Teilenummer	<a href="#">FQB5N30TM</a>
Hersteller	<a href="#">Fairchild/ON Semiconductor</a>
Beschreibung	MOSFET N-CH 300V 5.4A D2PAK
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	1450 pcs Stock
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-263-3, D <sup>2</sup> Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	D <sup>2</sup> PAK (TO-263AB)
Verlustleistung (max)	3.13W (Ta), 70W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	300V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	5.4A (Tc)
Rds On (Max) @ Id, Vgs	900 mOhm @ 2.7A, 10V
VGS (th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	13nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	430pF @ 25V
Verpackung	Tape & Reel (TR)


FQB5N30TM ist neu im Original, Suche FQB5N30TM Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FQB5N30TM Fairchild/ON Semiconductor mit Garantie und Vertrauen. Anfrage FQB5N30TM: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <b>FQB5N20L</b> VB FQB5N20L VB	 <b>FQB5N30TM</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 300V 5.4A D2PAK	 <b>FQB5N20LTM</b> Fairchild/ON Semiconductor MOSFET N-CH 200V 4.5A D2PAK	 <b>FQB5N40</b> Fairchild/ON Semiconductor FQB5N40 FAIRCHILD
 <b>FQB5N40TM</b> Fairchild/ON Semiconductor MOSFET N-CH 400V 4.5A D2PAK	 <b>FQB5N20LTM</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 200V 4.5A D2PAK	 <b>FQB5N50</b> FAIRCHILD FQB5N50 FAIRCHILD	 <b>FQB5N20TM</b> Fairchild/ON Semiconductor MOSFET N-CH 200V 4.5A D2PAK

### heiße Teile

Mehr

 FQB4N50TM	 FQB4N60C	 FQB4N80TM	 FQB4N80TM	 FQB4N90TM
 FQB4N90TM	 FQB4P25TM	 FQB4P25TM	 FQB5N03	 FQB5N06
 FQB50N06C	 FQB50N06L	 FQB50N06LTM	 FQB50N06LTM	 FQB50N06M
 FQB50N06TM	 FQB50N06TM	 FQB50N06TM-NL	 FQB55N06TM	 FQB55N06TM
 FQB55N10	 FQB55N10TM	 FQB55N10TM	 FQB5N20L	 FQB5N30TM
 FQB5N50C	 FQB5N50CF	 FQB5N50CTM	 FQB5N50CTM	 FQB5N60CTM
 FQB5N60CTM	 FQB5N90TM	 FQB5N90TM	 FQB5P10TM	 FQB5P10TM
 FQB630TM	 FQB630TM	 FQB65N06	 FQB65N06TM	 FQB65N06TM
 FQB6N40C	 FQB6N40CF	 FQB6N40CTM	 FQB6N40CTM	 FQB6N50TM
 FQB6N50TM	 FQB6N60C	 FQB6N60CTM	 FQB6N60CTM	 FQB6N60TM

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